

SEMITOP[®]4

3-phase bridge rectifier + brake chopper + 3-phase bridge inverter sk 100 DGDL 066 T

Preliminary Data

Features

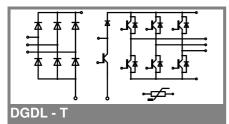
- One screw mounting module
- Fully compatible with SEMITOP[®]1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology free-wheeling diode
- Integrated NTC temperatur sensor

Typical Applications*

- Inverter up to 12,5 kVA
- Typical motor power 5,5 kW

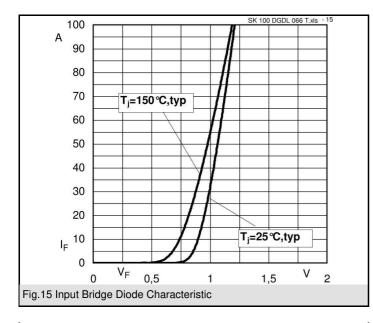
Remarks

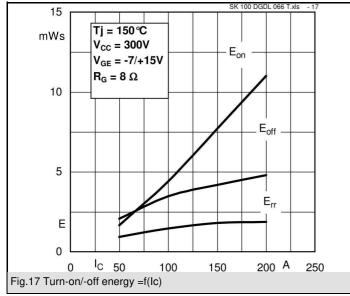
• V_{CE,sat} , V_F = chip level value

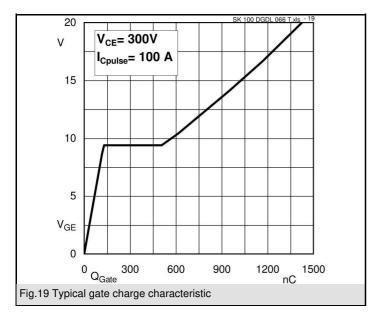


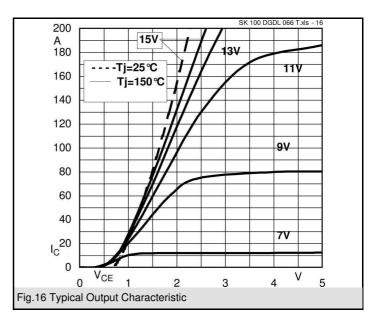
Absolute Maximum Ratings		T _s = 25°C, unless otherwise	T_s = 25°C, unless otherwise specified					
Symbol	Conditions	Values	Units					
IGBT - Inverter, Chopper								
V _{CES}		600	V					
I _C	T _s = 25 (70) °C, T _j = 175 °C	106 (85)	А					
I _C	T _s = 25 (70) °C, T _j = 150 °C	96 (73)	A					
I _{CRM}	$I_{CRM} = 2 \times I_{Cnom}, t_p = 1 \text{ ms}$	200	A					
V_{GES}		± 20	V					
Т _ј		-40 + 175	°C					
Diode - Ir	verter, Chopper							
I _F	T _s = 25 (70) °C, T _i = 150 °C	91 (67)	A					
I _F	T _s = 25 (70) °C, T _j = 175 °C	99 (79)	А					
I _{FRM}	$I_{FRM} = 2xI_{Fnom}, t_p = 1 ms$	200	А					
Diode - Rectifier								
V _{RRM}		800	V					
I _F	T _s = 70 °C	61	А					
I _{FSM}	t _p = 10 ms, sin 180 °, T _j = 25 °C	700	А					
i²t	t _p = 10 ms, sin 180 °, T _j = 25 °C	2400	A²s					
T _j		-40 + 175	°C					
T _{sol}	Terminals, 10 s	260	°C					
T _{stg}		-40 + 125	°C					
V _{isol}	AC, 1 min.	2500	V					

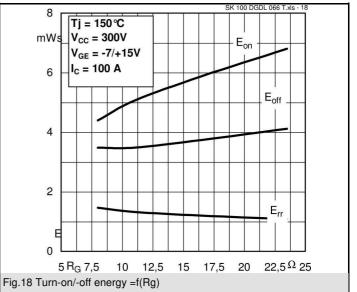
Characte	ristics	T_s = 25°C, unless otherwise specified							
Symbol	Conditions	min.	typ.	max.	Units				
IGBT - Inverter, Chopper									
V _{CE(sat)}	I _{Cnom} = 100 Å, T _j = 25 (150) °C	1,05	1,45 (1,7)	1,9 (2,15)	V				
V _{GE(th)}	$V_{GE} = V_{CE}, I_{C} = 1,6 \text{ mA}$	5	5,8	6,5	V				
V _{CE(TO)}	T _j = 25 (150) °C		0,9 (0,7)		V				
r _{CE}	$T_{j} = 25 (150) \ ^{\circ}C$		5,5 (10)	9 (13,5)	mΩ				
C _{ies}	V _{CE} = 25 V, V _{GE} = 0 V, f = 1 MHz		6,16		nF				
C _{oes}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,38		nF				
C _{res}	V_{CE} = 25 V, V_{GE} = 0 V, f = 1 MHz		0,18		nF				
R _{th(j-s)}	per IGBT		0,65		K/W				
t _{d(on)}	under following conditions		28		ns				
t _r	V_{CC} = 300 V, V_{GE} = - 7 / + 15 V		32		ns				
t _{d(off)}	I _{Cnom} = 100 A, T _j = 150 °C		301		ns				
t _f	$R_{Gon} = R_{Goff} = 8 \Omega$		45		ns				
$E_{on} \left(E_{off} \right)$	inductive load		4,4 (3,5)		mJ				
Diode - In	verter, Chopper								
$V_F = V_{EC}$	I _F = 100 A, T _j = 25 (150) °C		1,25 (1,2)		V				
V _(TO)	$T_{j} = 25 (150)^{\circ}C$		0,95 (0,85)		V				
r _T	T _j = 25 (150) °C		3 (3,5)		mΩ				
R _{th(j-s)}	per diode		0,8		K/W				
I _{RRM}	under following conditions		40		Α				
Q _{rr}	I _{Fnom} = 100 A, V _R = 300 V		5		μC				
E _{rr}	V _{GE} = 0 V, T _j = 150°C		1,45		mJ				
	di _F /dt = 2438 A/µs								
Diode - R	ectifier								
V _F	I _{Enom} = 35 A, T _i = 25 °C		1,1		V				
V _(TO)	T _i = 150 °C		0,8		V				
r _T	T _i = 150 °C		11		mΩ				
R _{th(j-s)}	per diode		0,9		K/W				
	Temperature Sensor								
R _{ts}	5 %, T _r = 25 (100) °C		5000(493)		Ω				
Mechanical Data									
w			60		g				
Ms	Mounting torque	2,5		2,75	Nm				

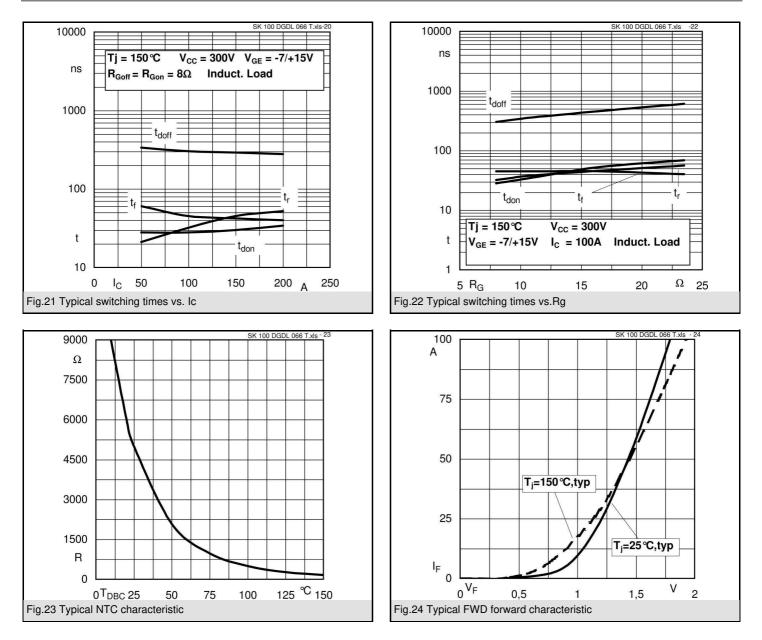


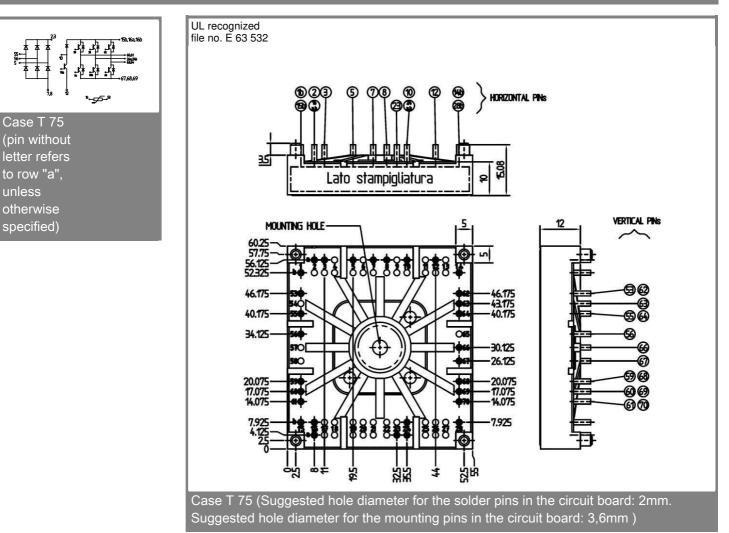












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.